

NTMFD4901NF

Dual N-Channel Power MOSFET with Integrated Schottky

30 V, High Side 18 A / Low Side 30 A, Dual N-Channel SO8FL

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

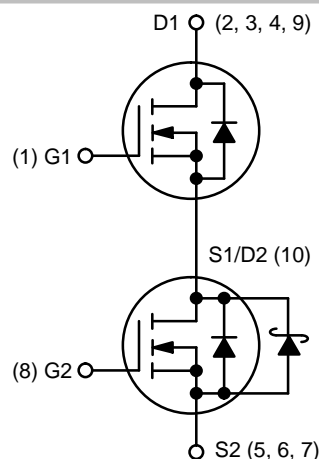
- DC-DC Converters
- System Voltage Rails
- Point of Load



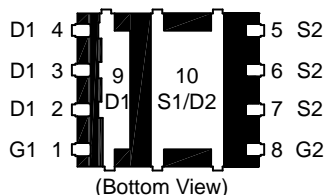
ON Semiconductor®

<http://onsemi.com>

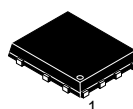
V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
Q1 Top FET 30 V	6.5 mΩ @ 10 V	18 A
	10 mΩ @ 4.5 V	
Q2 Bottom FET 30 V	2.35 mΩ @ 10 V	30 A
	3.5 mΩ @ 4.5 V	



PIN CONNECTIONS



MARKING DIAGRAM



DFN8
CASE 506BX



4901NF = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTMFD4901NF

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage	Q1	V _{DSS}	30	V		
Drain-to-Source Voltage	Q2					
Gate-to-Source Voltage	Q1	V _{GS}	±20	V		
Gate-to-Source Voltage	Q2					
Continuous Drain Current R _{θJA} (Note 1)	T _A = 25°C	Q1	I _D	13.5	A	
		Q2	23.4			
	T _A = 85°C	Q1	P _D	1.90		W
		Q2	2.07			
Power Dissipation R _{θJA} (Note 1)	T _A = 25°C	Q1	I _D	18.2	A	
		Q2	30.3			
	T _A = 85°C	Q1	P _D	3.45		W
		Q2	3.45			
Continuous Drain Current R _{θJA} ≤ 10 s (Note 1)	T _A = 25°C	Q1	I _D	10.3	A	
		Q2	17.9			
	T _A = 85°C	Q1	P _D	1.10		W
		Q2	1.20			
Power Dissipation R _{θJA} ≤ 10 s (Note 1)	T _A = 25°C	Q1	I _D	7.4	A	
		Q2	12.9			
	T _A = 85°C	Q1	P _D	1.10		W
		Q2	1.20			
Continuous Drain Current R _{θJA} (Note 2)	T _A = 25°C	Q1	I _{DM}	60	A	
		Q2	100			
	T _A = 85°C	Q1	T _J , T _{STG}	-55 to +150		°C
		Q2				
Power Dissipation R _{θJA} (Note 2)	T _A = 25°C	Q1	I _S	3.4	A	
		Q2	4.9			
Pulsed Drain Current	T _A = 25°C t _p = 10 μs	Q1	I _{DM}	60	A	
Operating Junction and Storage Temperature		Q1	T _J , T _{STG}	-55 to +150	°C	
		Q2				
Source Current (Body Diode)		Q1	I _S	3.4	A	
		Q2	4.9			
Drain to Source dV/dt			dV/dt	6	V/ns	
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, V _{DD} = 50 V, V _{GS} = 10 V, I _L = XX A _{pk} , L = 0.1 mH, R _G = 25 Ω)	24 A	Q1	EAS	28.8	mJ	
	48 A	Q2	EAS	115		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

NTMFD4901NF

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	Q1	R _{θJA}	65.9	°C/W
	Q2		60.5	
Junction-to-Ambient – Steady State (Note 4)	Q1	R _{θJA}	113.2	
	Q2		104	
Junction-to-Ambient – (t ≤ 10 s) (Note 3)	Q1	R _{θJA}	36.2	
	Q2		36.2	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Break-down Voltage	Q1	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
	Q2		V _{GS} = 0 V, I _D = 1 mA	30			
Drain-to-Source Break-down Voltage Temperature Coefficient	Q1	V _{(BR)DSS} / T _J			18		mV / °C
	Q2				15		
Zero Gate Voltage Drain Current	Q1	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1	μA
				T _J = 125°C		10	
	Q2		V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		500	
Gate-to-Source Leakage Current	Q1	I _{GSS}	V _{GS} = 0 V, V _{DS} = ±20 V			±100	nA
	Q2					±100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA		1.2		2.2	V
	Q2				1.2		2.2	
Negative Threshold Temperature Coefficient	Q1	V _{GS(TH)} / T _J				4.5		mV / °C
	Q2					4.0		
Drain-to-Source On Resistance	Q1	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A		5.2	6.5	mΩ
			V _{GS} = 4.5 V	I _D = 10 A		8.0	10	
	Q2		V _{GS} = 10 V	I _D = 20 A		1.9	2.35	
			V _{GS} = 4.5 V	I _D = 20 A		2.8	3.5	
Forward Transconductance	Q1	g _{FS}	V _{DS} = 1.5 V, I _D = 10 A			28		S
	Q2					45		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

NTMFD4901NF

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	Q1	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		1150		pF
	Q2				2950		
Output Capacitance	Q1	C _{OSS}			360		
	Q2				1100		
Reverse Capacitance	Q1	C _{RSS}			105		
	Q2				82		
Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 10 A		9.7		nC
	Q2				20		
Threshold Gate Charge	Q1	Q _{G(TH)}			1.1		
	Q2				2.7		
Gate-to-Source Charge	Q1	Q _{GS}			3.3		
	Q2				7.3		
Gate-to-Drain Charge	Q1	Q _{GD}			3.7		
	Q2			5.3			
Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V; I _D = 10 A		19.1		nC
	Q2				42.7		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 10 A, R _G = 3.0 Ω		9.0		ns
	Q2				14		
Rise Time	Q1	t _r			15		
	Q2				16		
Turn-Off Delay Time	Q1	t _{d(OFF)}			14		
	Q2				25		
Fall Time	Q1	t _f			4.0		
	Q2				7.0		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 10 A, R _G = 3.0 Ω		6.0		ns
	Q2				10		
Rise Time	Q1	t _r			14		
	Q2				15		
Turn-Off Delay Time	Q1	t _{d(OFF)}			17		
	Q2				32		
Fall Time	Q1	t _f			3.0		
	Q2				5.0		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

NTMFD4901NF

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Voltage	Q1	V _{SD}	V _{GS} = 0 V, I _S = 3 A	T _J = 25°C	0.75	1.0	V
				T _J = 125°C	0.62		
	Q2		V _{GS} = 0 V, I _S = 2 A	T _J = 25°C	0.45	0.70	
				T _J = 125°C	0.37		
Reverse Recovery Time	Q1	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 3 A		23		ns
	Q2				40		
Charge Time	Q1	t _a			12		
	Q2				21		
Discharge Time	Q1	t _b			11		
	Q2				19		
Reverse Recovery Charge	Q1	Q _{RR}			12		nC
	Q2				40		

PACKAGE PARASITIC VALUES

Source Inductance	Q1	L _S	T _A = 25°C		0.38		nH
	Q2				0.65		
Drain Inductance	Q1	L _D			0.054		nH
	Q2				0.007		
Gate Inductance	Q1	L _G			1.5		nH
	Q2				1.5		
Gate Resistance	Q1	R _G			0.8		Ω
	Q2				0.8		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTMFD4901NFT1G	DFN8 (Pb-Free)	1500 / Tape & Reel
NTMFD4901NFT3G	DFN8 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – Q1

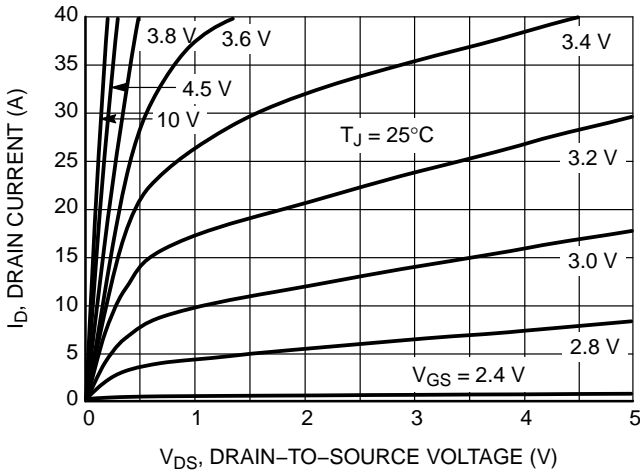


Figure 1. On-Region Characteristics

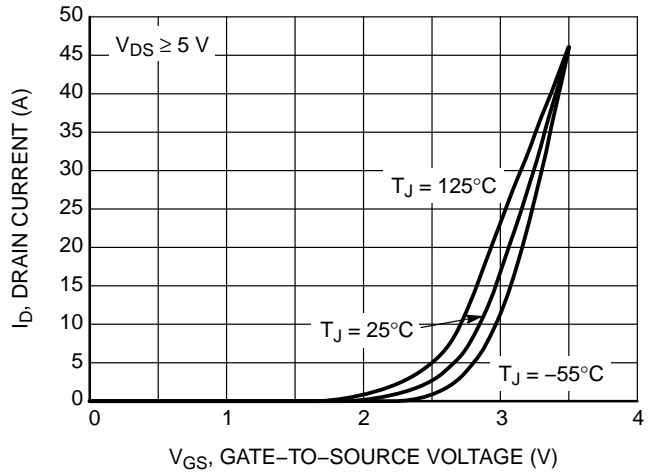


Figure 2. Transfer Characteristics

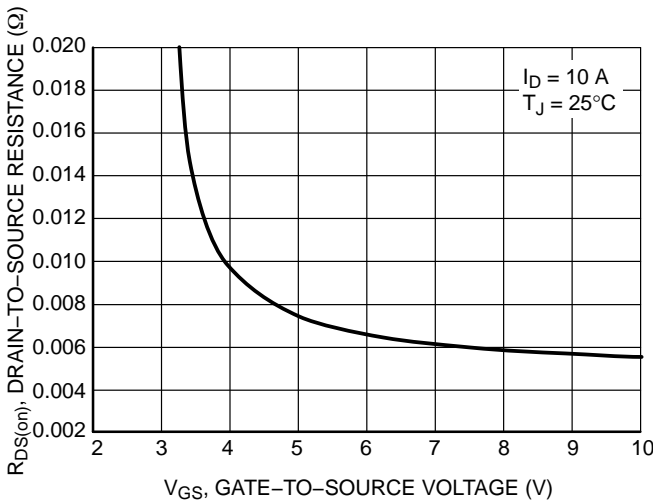


Figure 3. On-Resistance vs. Gate-to-Source Resistance

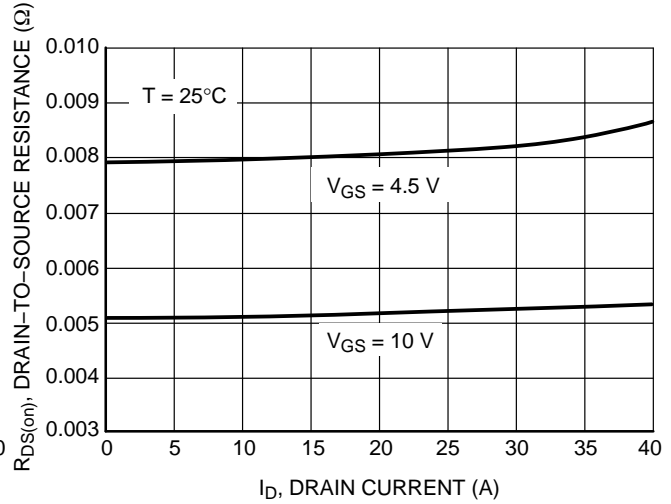


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

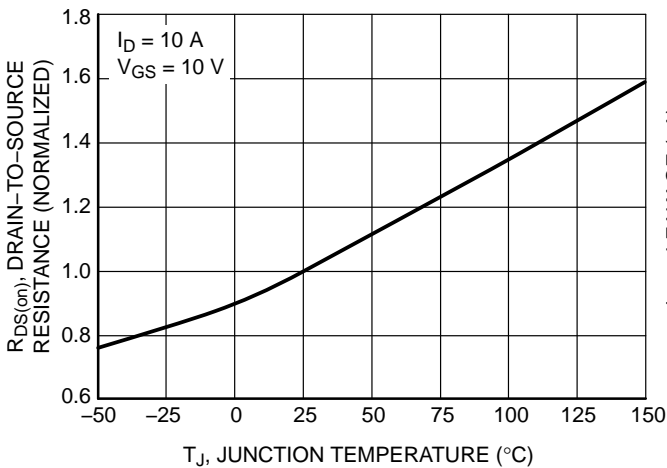


Figure 5. On-Resistance Variation with Temperature

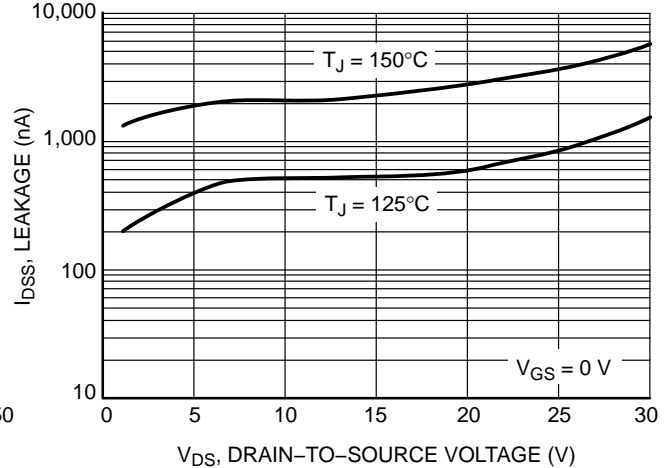


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTMFD4901NF

TYPICAL CHARACTERISTICS – Q1

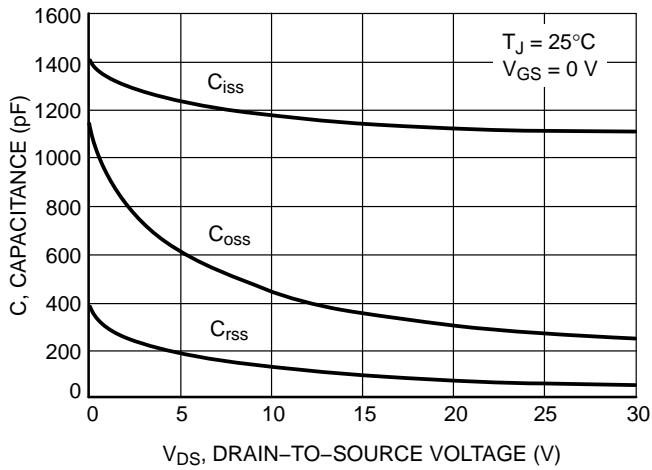


Figure 7. Capacitance Variation

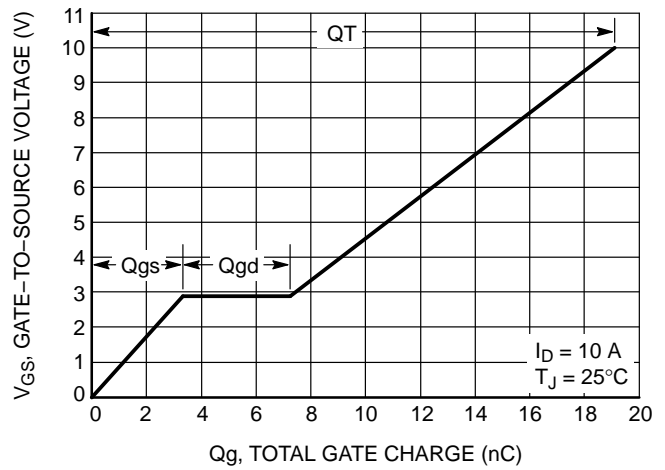


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

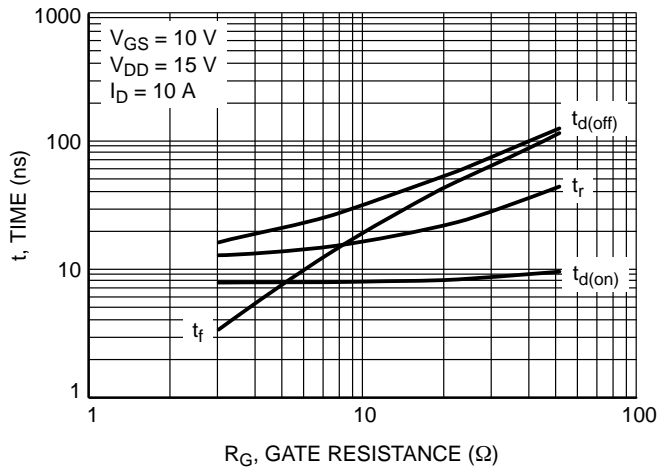


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

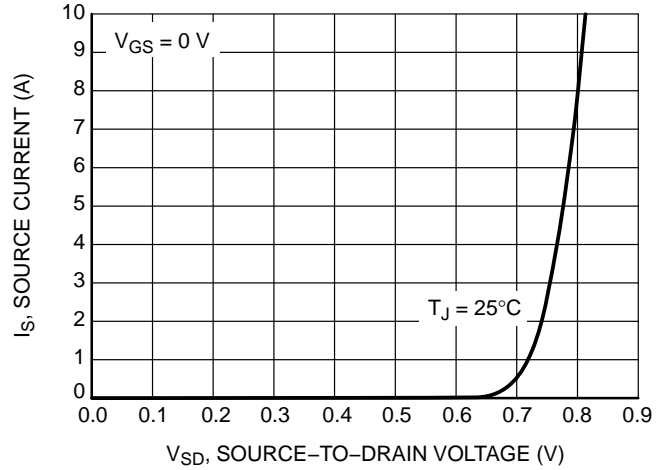


Figure 10. Diode Forward Voltage vs. Current

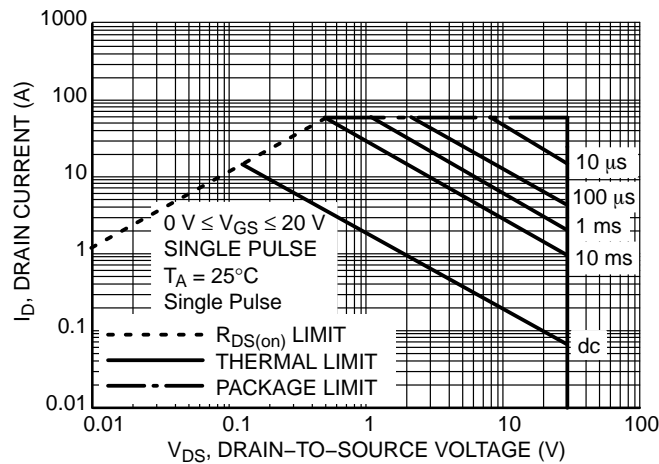


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTMFD4901NF

TYPICAL CHARACTERISTICS – Q1

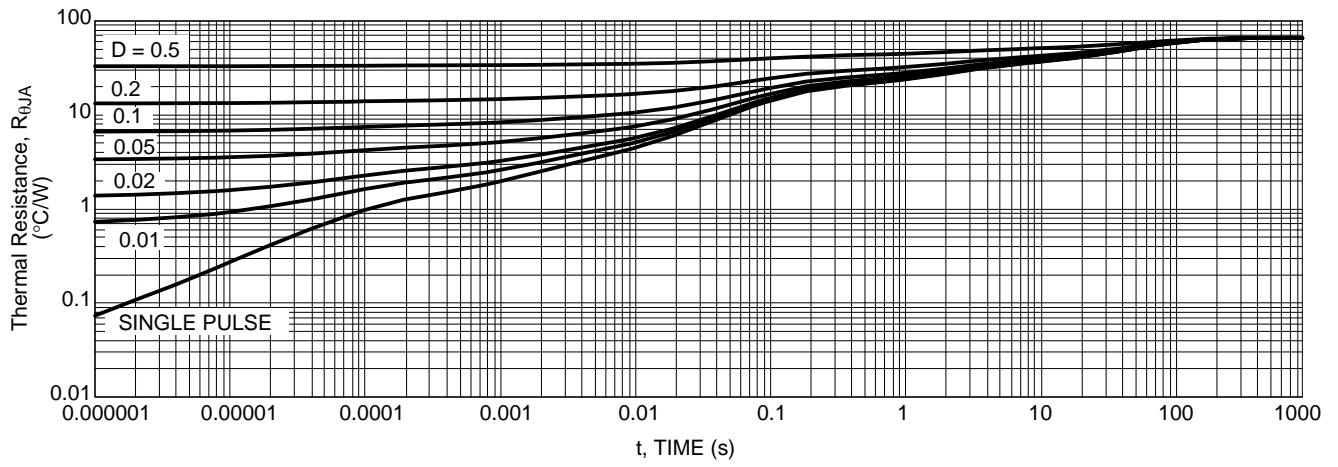


Figure 12. Thermal Response

TYPICAL CHARACTERISTICS – Q2

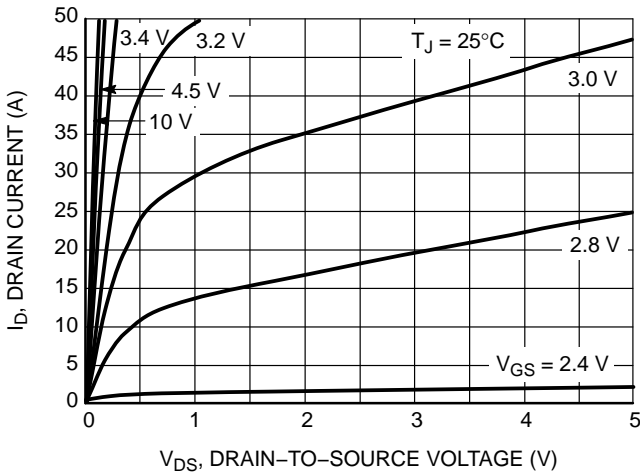


Figure 13. On-Region Characteristics

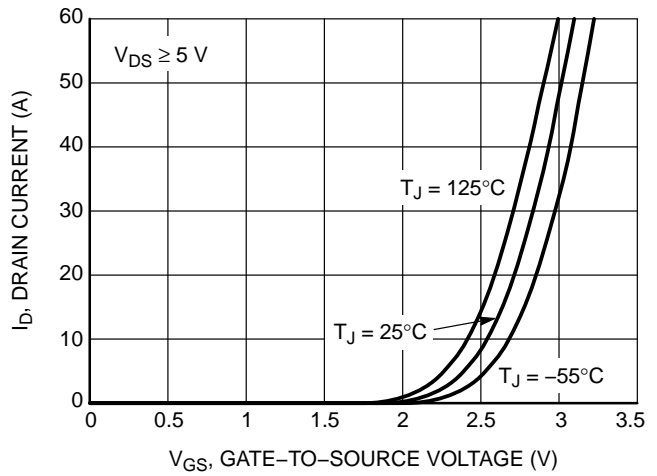


Figure 14. Transfer Characteristics

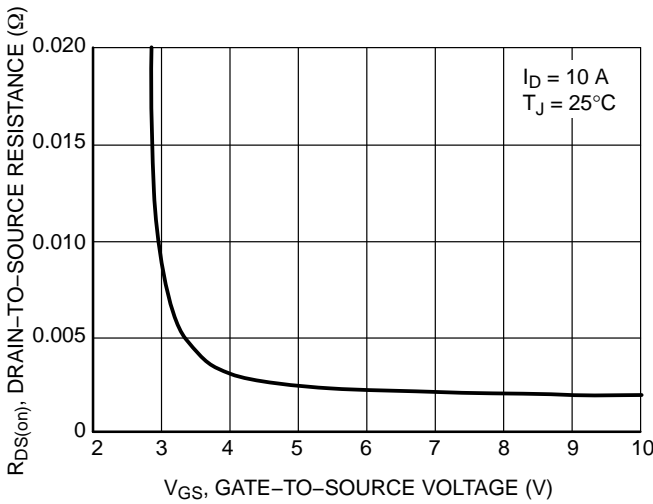


Figure 15. On-Resistance vs. Gate-to-Source Resistance

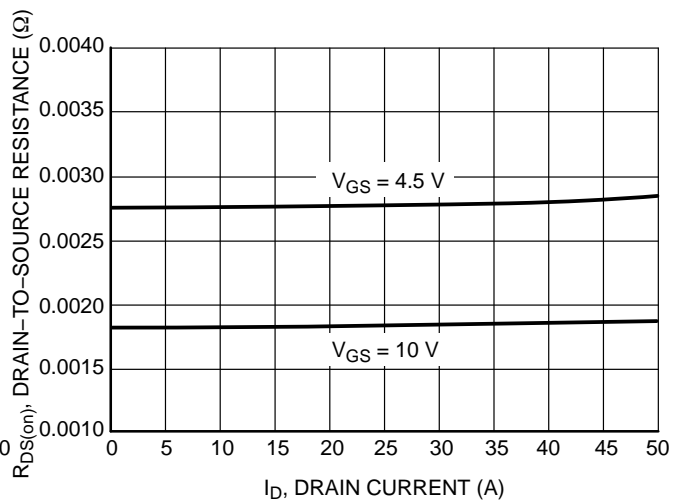


Figure 16. On-Resistance vs. Drain Current and Gate Voltage

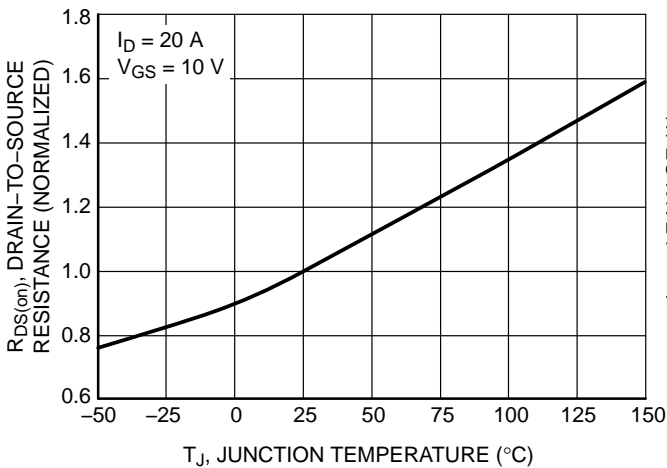


Figure 17. On-Resistance Variation with Temperature

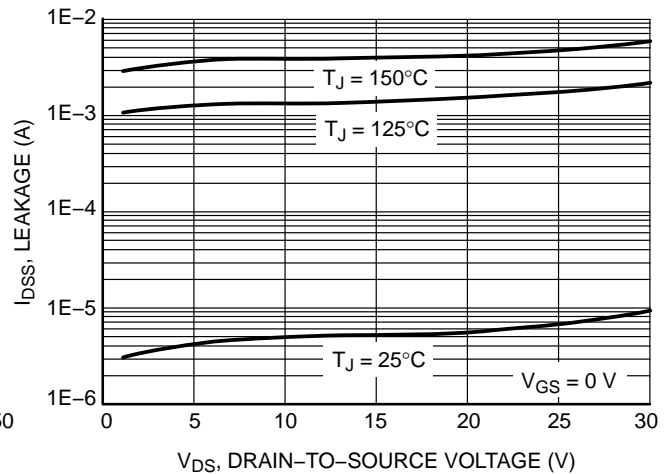


Figure 18. Drain-to-Source Leakage Current vs. Voltage

NTMFD4901NF

TYPICAL CHARACTERISTICS – Q2

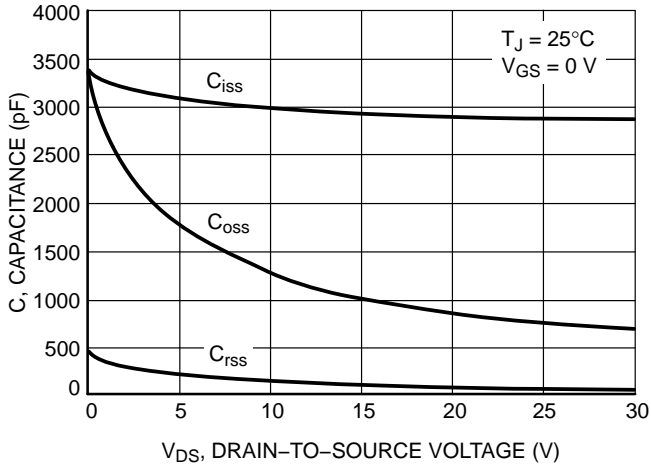


Figure 19. Capacitance Variation

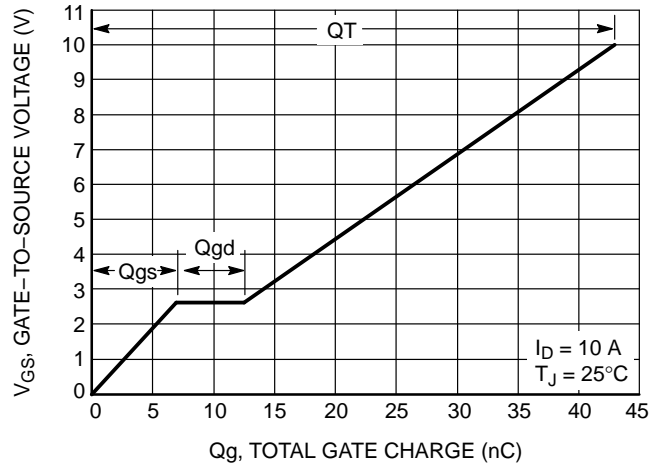


Figure 20. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

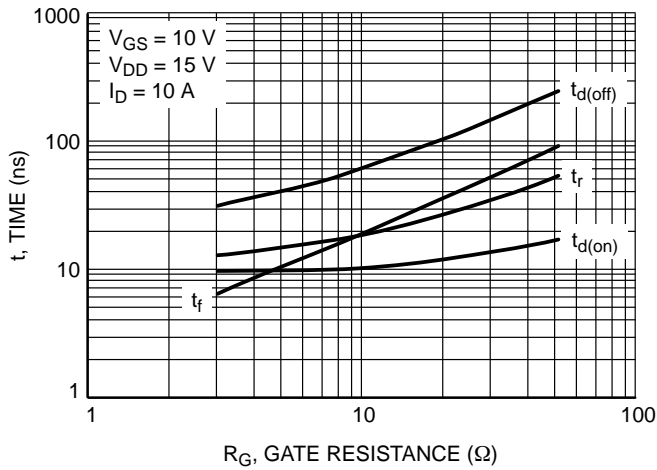


Figure 21. Resistive Switching Time Variation vs. Gate Resistance

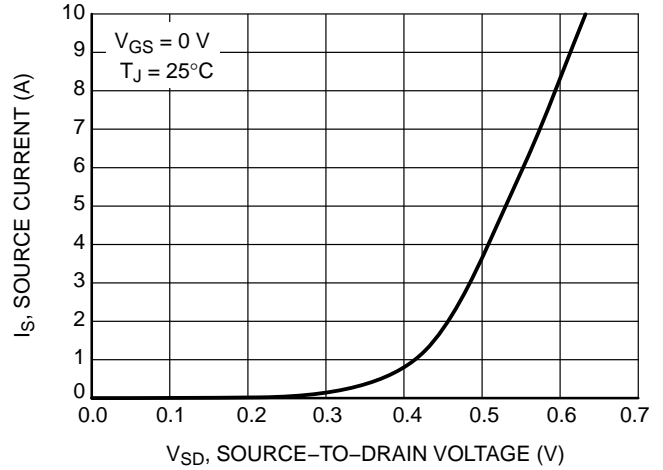


Figure 22. Diode Forward Voltage vs. Current

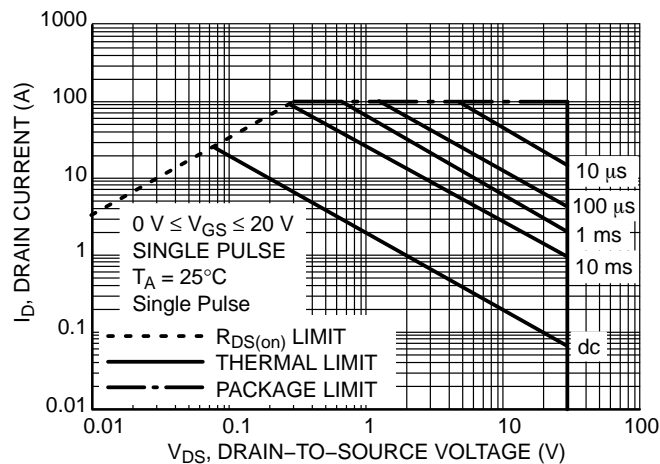


Figure 23. Maximum Rated Forward Biased Safe Operating Area

NTMFD4901NF

TYPICAL CHARACTERISTICS – Q2

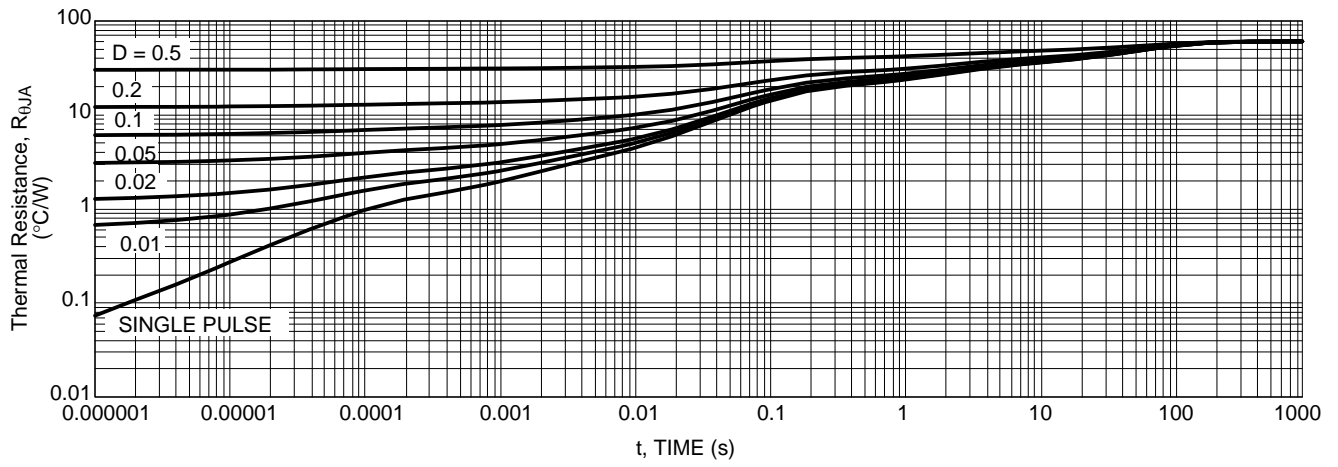
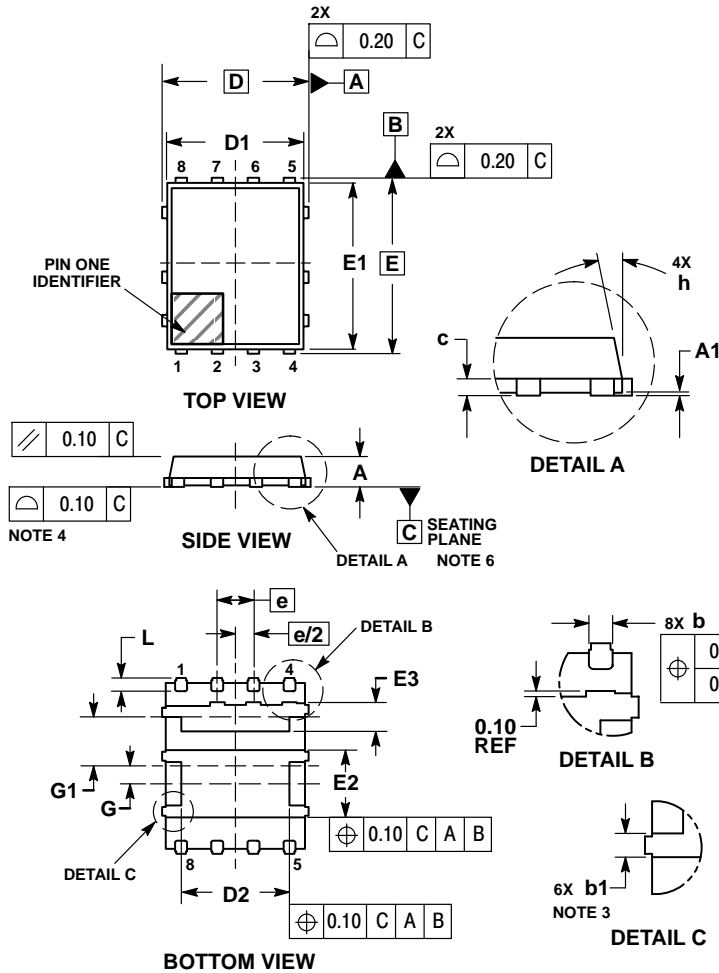


Figure 24. Thermal Response

NTMFD4901NF

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL-Dual-Asymmetrical) CASE 506BX ISSUE C

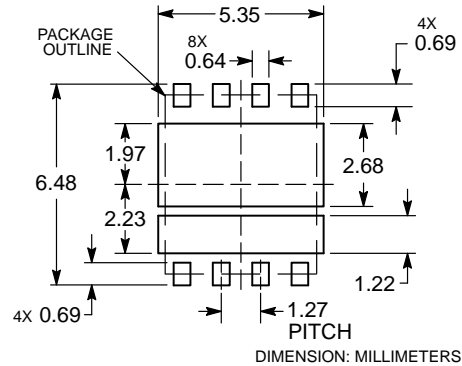


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b AND b1 APPLY TO PLATED FEATURES AND ARE MEASURED BETWEEN 0.15 AND 0.25 MM FROM TERMINAL TIPS.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
A1	0.00	0.05
b	0.41	0.61
b1	0.41	0.61
c	0.23	0.33
D	5.15 BSC	
D1	4.50	5.10
D2	3.50	4.22
E	6.15 BSC	
E1	5.50	6.10
E2	2.27	2.67
E3	0.82	1.22
e	1.27 BSC	
G	0.63 BSC	
G1	1.72 BSC	
h	12 °	
L	0.35	0.55

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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